

## Ted Johansson, LIST OF PUBLICATIONS

updated 2023-06-28

### 1           REGULAR PAPERS (peer-reviewed)

1. H. Norström, S. Nygren, T. Johansson, R. Buchta, M. Östling, A. Lindberg, U. Gustafsson, C. S. Petersson, "A Refined Polycide Gate Process With Silicided Diffusions for Submicron MOS Applications", *J. Electrochem. Soc.*, 136, 805 (1989).  
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3. T. Johansson, K. Jarl, M. Willander, "Power Amplifier for Ultra High Frequency using Conventional Silicon NMOS Technology", *Solid State Electronics*, 35, 213 (1992).  
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4. H. Norström, T. Johansson, J. Vanhellefont, K. Maex, "A Study of High Dose As and BF<sub>2</sub> Implantations into SIMOX Materials". *Semiconductor Science and Technology*, 8, 630 (1993).  
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12. B. G. Malm, E. Haralson, T. Johansson, M. Östling, "Self-Heating Effects in a BiCMOS on SOI Technology for RFIC Applications", *Trans. El. Dev.*, Vol. 52, No. 7, p. 1423, 2005. doi:10.1109/TED.2005.850634
13. T. Johansson, B.G. Malm, H. Norström, U. Smith, M. Östling, "Influence of SOI-generated stress on BiCMOS performance", *Solid-State Electronics*, 50, 935 (2006). doi:10.1016/j.sse.2006.04.034
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25. P. Rangaiah, J. Engstrand, T. Johansson, M. Perez and Robin Augustine, "92 Mb/s fat-intrabody communication (Fat-IBC) with low-cost WLAN hardware", accepted for publication in IEEE Transactions on Biomedical Engineering, 2023.

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- 37.N. Zimmermann, T. Johansson, S. Heinen, "Power Amplifiers in 0.13  $\mu\text{m}$  CMOS for DECT: A Comparison Between Two Different Architectures", RFIT 2007, Singapore, Dec 9-11, 2007. doi:10.1109/RFIT.2007.4443983

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- 45.M. F. U. Haque, T. Johansson, D. Liu, "Combined RF and Multilevel PWM Switch Mode Power Amplifier", Norchip 2013, Vilnius, Lithuania, Nov 11-12, 2013. doi:10.1109/NORCHIP.2013.6702010
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- 48.M. F. U. Haque, T. Johansson, D. Liu, "Combined RF and multiphase PWM Transmitter", ECCTD2015, Trondheim, Norway, Aug 24-26, 2015. doi: 10.1109/ECCTD.2015.7299999



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- 50.M. F. U. Haque, T. Johansson, D. Liu, "Large Dynamic Range PWM Transmitter", presented at Gigahertz 2016 symposium, Linköping, Sweden, Mar 15-16, 2016.
- 51.T. Johansson, O. Najari, and M. Carlsson, "Linear CMOS-PA design in different 28 nm technologies", presented at Gigahertz 2016 symposium, Linköping, Sweden, Mar 15-16, 2016.
- 52.O. Morales Chacón, T. Johansson, T. Flink, "The effect of DPD bandwidth limitation on EVM for a 28 nm WLAN 802.11ac transmitter", NORCAS 2017, Linköping, Sweden, Oct 23-25, 2017. doi: 10.1109/NORCHIP.2017.8124943
- 53.M. T. Pasha, M. F. U. Haque, J. Ahmad, T. Johansson, "An All-Digital Polar PWM Transmitter", presented at Gigahertz 2018 symposium, Lund, Sweden, May 24-25, 2018.
- 54.T. Johansson, O. Morales Chacón, T. Flink, "Digital predistortion with bandwidth limitations for a 28 nm WLAN 802.11ac transmitter", presented at Gigahertz 2018 symposium, Lund, Sweden, May 24-25, 2018.
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- 56.T. Johansson, S. Samji, "On the Design of a CMOS-integrated Load Modulated Balanced Amplifier", presented at NORCAS 2020, Oslo, Norway, Oct 27-28, 2020.
- 57.T. Johansson, P. Rangaiah, J. Engstrand, M. Perez, and R. Augustine, "Fat-layer intra-body communication", presented at Swedish Microwave Days, Stockholm May 23-25, 2023.

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3. T. Johansson, O. Bengtsson, S. Lotfi, L. Vestling, H. Norström, J. Olsson, C. Nyström, "A linear 32.8 dBm 2.4 GHz LDMOS power amplifier in 65 nm CMOS", SSoCC'13, Ystad, Sweden, May 6-7, 2013.
4. M. F. U. Haque, T. Johansson, D. Liu, "Modified Multilevel PWM Switch Mode Power Amplifier", SSoCC'14, Vadstena, Sweden, May 12-13, 2014.
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## 6 Lic. Eng. Thesis.

T. Johansson, "Process and Device Development of MOSFET Technologies for Telecommunication Applications", Linköping Studies in Science and Technology, Thesis No. 375. Presented at LiU June 2, 1993. ISBN 91-7871-115-0

## 7 Ph.D. Thesis.

T. Johansson, "The transistor, with emphasis on its use for radio frequency telecommunication.", Linköping Studies in Science and Technology, Dissertation No. 508. Presented at LiU, February 13, 1998. ISBN 91-7219-110-4